

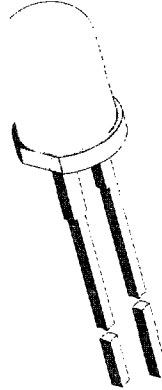
Silicon PIN Photodiode

Description

BPW43 is a very high speed PIN photodiode in a standard T-1 $\frac{3}{4}$ plastic package. Due to its waterclear epoxy the device is sensitive to visible and infrared radiation. It features low capacitance and high speed even at low supply voltages.

Features

- Extra fast response times
- Radiant sensitive area $A=0.78\text{mm}^2$
- Standard T-1 $\frac{3}{4}$ (ϕ 5 mm) clear package
- Angle of half sensitivity $\phi = \pm 25^\circ$
- Suitable for visible and near infrared radiation



948391

Applications

High speed photo detector

Absolute Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$

| Parameter | Test Conditions | Symbol | Value | Unit |
|-------------------------------------|---|-------------------|------------|------------------|
| Reverse Voltage | | V_R | 32 | V |
| Power Dissipation | $T_{\text{amb}} \cong 25^\circ\text{C}$ | P_V | 215 | mW |
| Junction Temperature | | T_j | 100 | $^\circ\text{C}$ |
| Storage Temperature Range | | T_{stg} | -25...+100 | $^\circ\text{C}$ |
| Soldering Temperature | $t \cong 3\text{ s}$ | T_{sd} | 245 | $^\circ\text{C}$ |
| Thermal Resistance Junction/Ambient | | R_{thJA} | 350 | K/W |

Basic Characteristics

$T_{amb} = 25^{\circ}\text{C}$

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|--------------------------------|--|-----------------|-----|------------|-----|---------------|
| Breakdown Voltage | $I_R = 100 \mu\text{A}, E = 0$ | $V_{(BR)}$ | 32 | | | V |
| Reverse Dark Current | $V_R = 10 \text{ V}, E = 0$ | I_{r0} | | 1 | 10 | nA |
| Diode Capacitance | $V_R = 0 \text{ V}, f = 1 \text{ MHz}, E = 0$ | C_D | | 4 | | pF |
| | $V_R = 5 \text{ V}, f = 1 \text{ MHz}, E = 0$ | C_D | | 1.5 | | pF |
| | $V_R = 10 \text{ V}, f = 1 \text{ MHz}, E = 0$ | C_D | | 1.3 | | pF |
| Open Circuit Voltage | $E_A = 1 \text{ klx}$ | V_o | | 320 | | mV |
| Short Circuit Current | $E_A = 1 \text{ klx}$ | I_k | | 12 | | μA |
| | $E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$ | I_k | | 6 | | μA |
| Reverse Light Current | $E_A = 1 \text{ klx}, V_R = 5 \text{ V}$ | I_{rA} | | 15 | | μA |
| | $E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_R = 5 \text{ V}$ | I_{rA} | 4 | 8 | | μA |
| Angle of Half Sensitivity | | ϕ | | ± 25 | | deg |
| Wavelength of Peak Sensitivity | | λ_p | | 900 | | nm |
| Range of Spectral Bandwidth | | $\lambda_{0.5}$ | | 550...1000 | | nm |
| Rise Time | $V_R = 10 \text{ V}, R_L = 50 \Omega, \lambda = 820 \text{ nm}$ | t_r | | 4 | | ns |
| Fall Time | $V_R = 10 \text{ V}, R_L = 50 \Omega, \lambda = 820 \text{ nm}$ | t_f | | 4 | | ns |

Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)

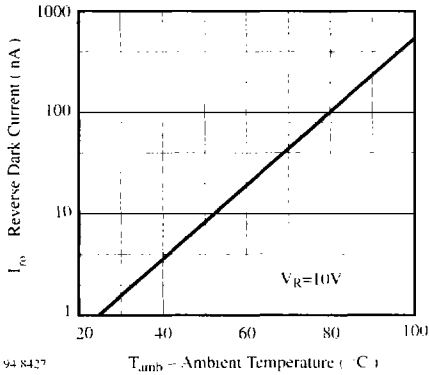


Figure 1. Reverse Dark Current vs. Ambient Temperature

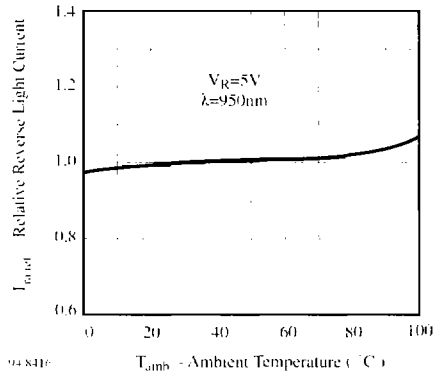


Figure 2. Relative Reverse Light Current vs. Ambient Temperature

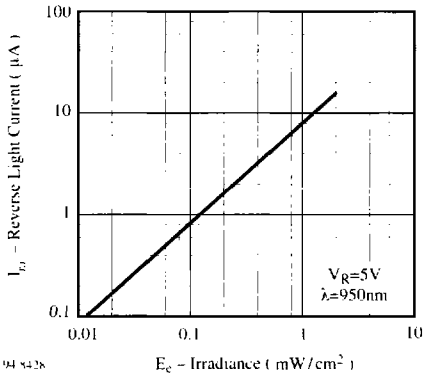


Figure 3. Reverse Light Current vs. Irradiance

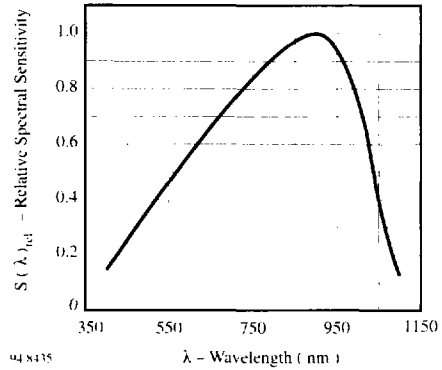


Figure 6. Relative Spectral Sensitivity vs. Wavelength

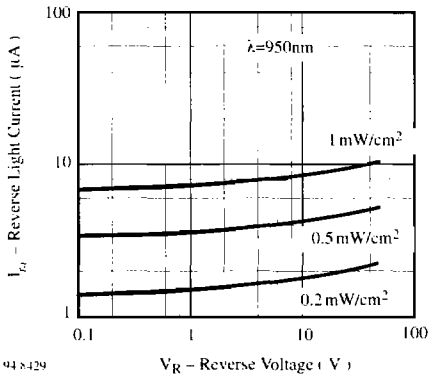


Figure 4. Reverse Light Current vs. Reverse Voltage

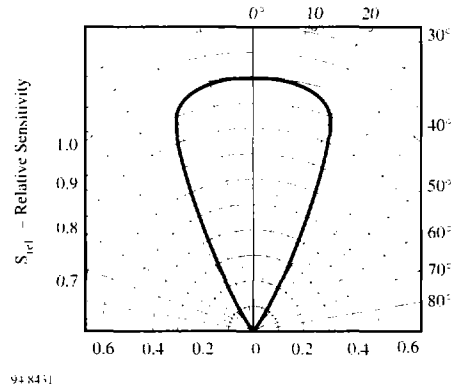


Figure 7. Relative Radiant Sensitivity vs. Angular Displacement

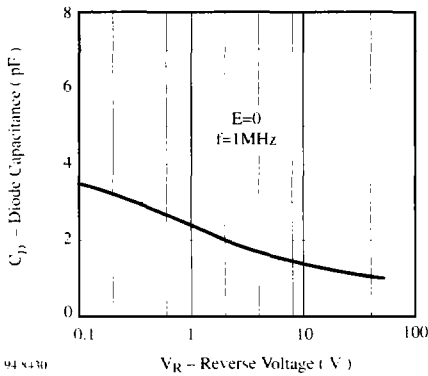
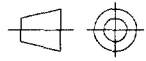
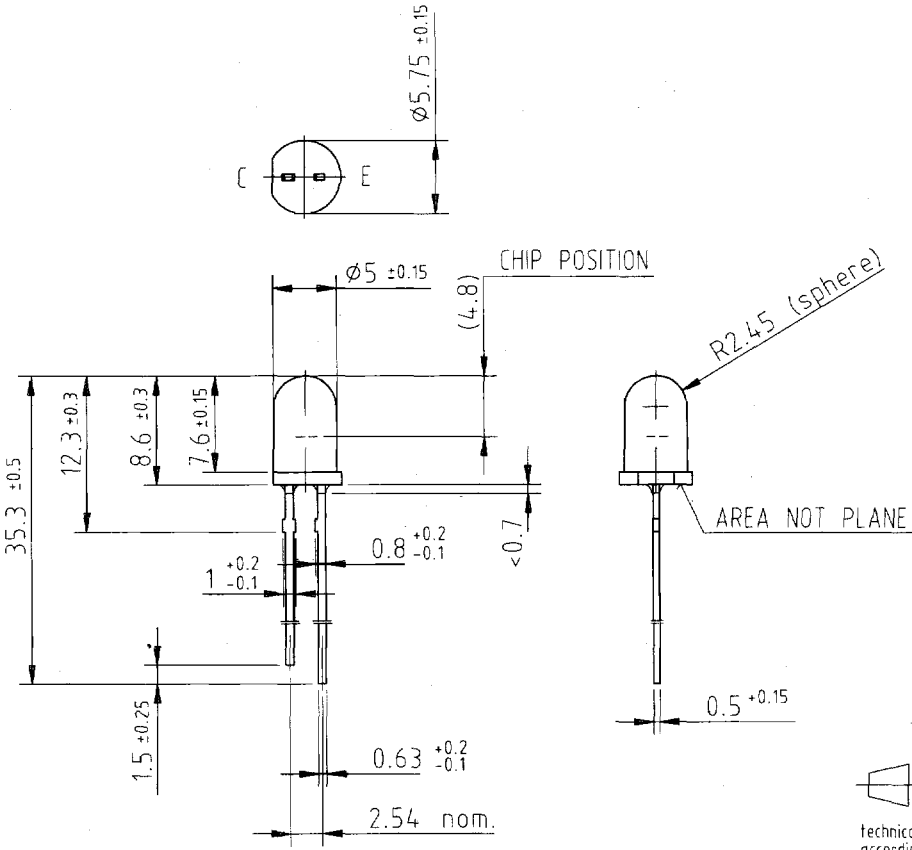


Figure 5. Diode Capacitance vs. Reverse Voltage

Dimensions in mm



technical drawings according to DIN specifications

96 12192

